
2.

[3-8]

SG -

SG-

3.

4.

100

10^{-2}

MG-

.2.

, (.2),

Ti, Al, S, P, C

20%..

« » (.1).

-21,

Cu-K
()

JEOL TECHNICS.

MG-Si

	% ()		%
	mg-Si	mg-Si	
Cu	0,016	0,002	87,5
Al	0,21	0,055	73,8
Ca	0,26	0,13	50
Fe	1	0,8	20
P	0,006	0,005	17
S	0,02	0,001	95
C	0,12	0,015	87,5
Cr	0,066	0,044	33
Ti	0,32	0,032	90
-	2,018	1,084	46,31
Si	97,982	98,916	-



.1.

(HNO₃ + HF).

7\ 2.

(.2).

6-

. 3.

(.3,)

-1

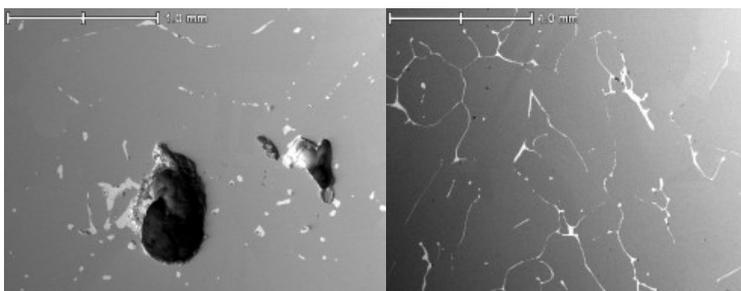
2,

,

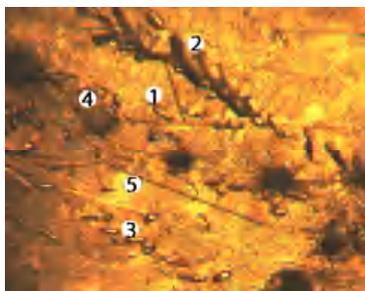
4,

5.

3,



2. —, . 50 —, —
 , 1 2- — 2.
 , , .

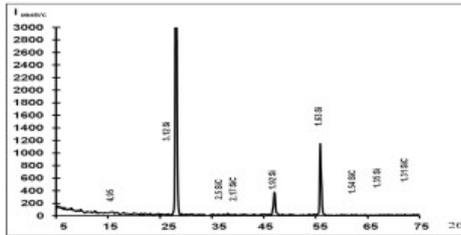
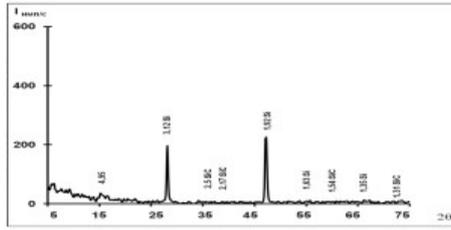


3. : — , — —
 , 200

=4,95). : Si, SiC (d_{hkl})

JEOL TECHNICS

4. 10-20 , —
 , — SiC.



3. ; -



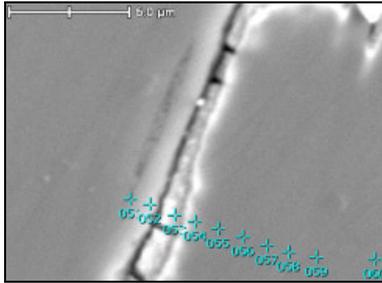
x1500

	C	Al	Si	Ca	Cr	Fe	,%
003			100.0				100
004	14.12	1.54	81.70	2.64			100
007	13.78	1.19	83.47	1.55			100
009		1.39	41.16		1.23	56.22	100

4. 1, ; -

Si -

() (.5).
 .5, FeSi FeSi₂, -
 , .3, .



x8000

	Al	Si	Ca	Fe	Ni	,%
051		100.0				100
052	1.14	98.86				100
053	12.47	44.79	5.39	35.28	2.08	100
054	12.33	54.29	4.96	26.95	1.47	100
055	6.09	81.33	2.36	10.22		100
056	2.35	94.53		3.11		100
057	0.93	99.07				100
058	0.67	99.33				100
059	0.54	99.46				100
060		100.0				100

.5.

_____ ;
 50% Cu -
 87,6%, Al -73,8%, S- 95%, C- 87,5%, Ti -90%,

0,2-2,0

: Ca, Cr, Fe, Ni, Al

Fe, Al, Cr, Ni

Ca,

SG-

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